Masaya Hamada

List of Publications by Year
in descending order

12	67	1683354 5	1588620 8
papers	citations	h-index	g-index

12	12	12	62
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Elucidation of PVD MoS₂ film formation process and its structure focusing on sub-monolayer region. Japanese Journal of Applied Physics, 2022, 61, SC1023.	0.8	5
2	Positive Seebeck coefficient of niobium-doped MoS₂ film deposited by sputtering and activated by sulfur vapor annealing. Japanese Journal of Applied Physics, 2022, 61, 075506.	0.8	1
3	Sheet Resistance Reduction of MoSâ„‚ Film Using Sputtering and Chlorine Plasma Treatment Followed by Sulfur Vapor Annealing. IEEE Journal of the Electron Devices Society, 2021, 9, 278-285.	1.2	10
4	Self-aligned-TiSi2 bottom contact with APM cleaning and post-annealing for sputtered-MoS2 film. Japanese Journal of Applied Physics, 2021, 60, SBBH04.	0.8	0
5	ZrS₂ symmetrical-ambipolar FETs with near-midgap TiN film for both top-gate electrode and Schottky-barrier contact. Japanese Journal of Applied Physics, 2021, 60, SBBH05.	0.8	8
6	Importance of crystallinity improvement in MoS₂ film by compound sputtering even followed by post sulfurization. Japanese Journal of Applied Physics, 2021, 60, SBBH10.	0.8	7
7	WS2 Film by Sputtering and Sulfur-Vapor Annealing, and its pMISFET with TiN/HfO2 Top-Gate Stack, TiN Bottom Contact, and Ultra-Thin Body and Box. IEEE Journal of the Electron Devices Society, 2021, , 1-1.	1.2	3
8	Side-Contact Architecture for p/n-Stacked-Nano-Sheet ZrS2 2D-FETs Beyond 1-nm Technology Node. , 2021, , .		0
9	Hall-effect mobility enhancement of sputtered MoS₂ film by sulfurization even through Al₂O₃ passivation film simultaneously preventing oxidation. Japanese Journal of Applied Physics, 2020, 59, 105501.	0.8	7
10	Normally-off sputtered-MoS2 nMISFETs with TiN top-gate electrode all defined by optical lithography for chip-level integration. Japanese Journal of Applied Physics, 2020, 59, 080906.	0.8	6
11	High Hall-Effect Mobility of Large-Area Atomic-Layered Polycrystalline ZrS₂Film Using UHV RF Magnetron Sputtering and Sulfurization. IEEE Journal of the Electron Devices Society, 2019, 7, 1258-1263.	1.2	17
12	High Seebeck coefficient in PVD-WS2 film with grain size enlargement. Japanese Journal of Applied Physics, 0, , .	0.8	3